

Features

- Low drain-source on-resistance: $R_{DS(ON)}=0.257\Omega$ (typ)
- Easy to control gate switching
- Enhancement mode: $V_{th} = 2.8$ to $4.2V$
- 100% avalanche tested
- RoHS compliant

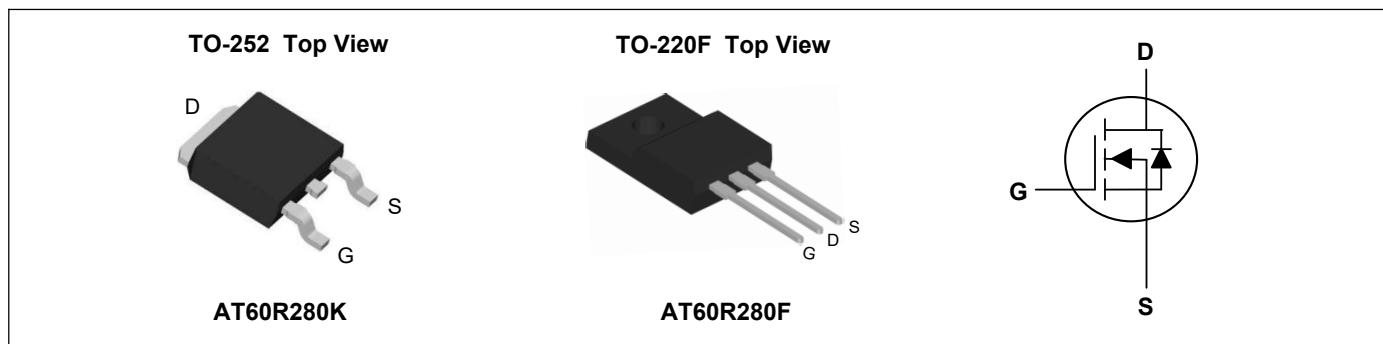
Key Performance Parameters



Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	600	V
$R_{DS(ON),max}$	280	mΩ
I_D	15	A
$Q_{g,typ}$	23	nC
I_{DM}	45	A

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger, Lighting.



Absolute Maximum Ratings($T_c=25^\circ C$, unless otherwise noted)

Parameter	Symbol	TO-252	TO-220F	Unit
Drain-Source Voltage	V_{DS}	600		V
Gate-Source Voltage	V_{GS}	± 30		V
Continuous Drain Current ¹	I_D @ $T_c=25^\circ C$	15		A
Pulsed Drain Current ²	I_{DM}	45		A
Single Pulse Avalanche Energy	EAS	405		mJ
MOSFET dv/dt ruggedness, $V_{DS} = 0\dots 400V$	dv/dt	50		V/ns
Reverse diode dv/dt ³ $V_{DS}=0\dots 400V$, $I_{SD}\leq 48A$, $T_j=25^\circ C$		15		
Total Power Dissipation ($T_c=25^\circ C$)	P_D	118	32	W
Storage Temperature Range	T_{STG}	-55 to 150		°C
Operating Junction Temperature Range	T_J	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	TO-252	TO-220F	Unit
		Max	Max	
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	62	80	°C/W
Thermal Resistance Junction-Case	$R_{\theta JC}$	1.06	3.9	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}$, $I_D=10\text{mA}$	605	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$, $I_D=7.5\text{A}$	---	240	280	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$, $I_D = 250\text{\mu A}$	2.5	---	4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=600\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	100	nA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 30\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
Gate Resistance	R_G	$f = 1.0\text{MHz}$, open drain	---	5.3	---	Ω
Total Gate Charge	Q_g	$V_{\text{DD}}=400\text{V}$, $V_{\text{GS}}=10\text{V}$, $I_D=3.8\text{A}$	---	23	---	nC
Gate-Source Charge	Q_{gs}		---	5.7	---	
Gate-Drain Charge	Q_{gd}		---	17	---	
Gate Plateau Voltage	V_{plateau}		---	5.4	---	V
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{DD}}=400\text{V}$, $V_{\text{GS}}=10\text{V}$, $R_G=10\Omega$, $I_D=3.8\text{A}$	---	8.4	---	ns
Rise Time	T_r		---	21.2	---	
Turn-Off Delay Time	$T_{\text{d(off)}}$		---	32.2	---	
Fall Time	T_f		---	20.8	---	
Input Capacitance	C_{iss}	$V_{\text{DS}}=50\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	820	---	pF
Output Capacitance	C_{oss}		---	58	---	
Reverse Transfer Capacitance	C_{rss}		---	3.1	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage	V_{SD}	$V_{\text{G}}=0\text{V}$, $I_F=1\text{A}$, $T_J=25^\circ\text{C}$	---	0.74	---	V
Reverse Recovery Time	t_{rr}	$V_R=400\text{V}$, $I_F=2\text{ A}$, $dI_F/dt=100\text{A}/\mu\text{s}$	---	216	---	ns
Reverse Recovery Charge	Q_{rr}		---	1.3	---	uC
Peak Reverse Recovery Current	I_{rrm}		---	16.6	---	A

Note:

1. Limited by $T_{j,\text{max}}$. Maximum Duty Cycle D = 0.50
2. Pulse width t_p limited by $T_{j,\text{max}}$
3. Identical low side and high side switch with identical R_G

Typical Characteristics

Figure 1. Output Characteristics

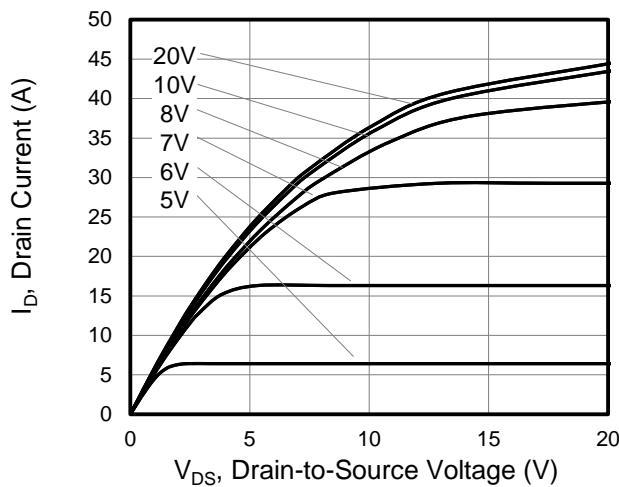


Figure 2. Transfer Characteristics

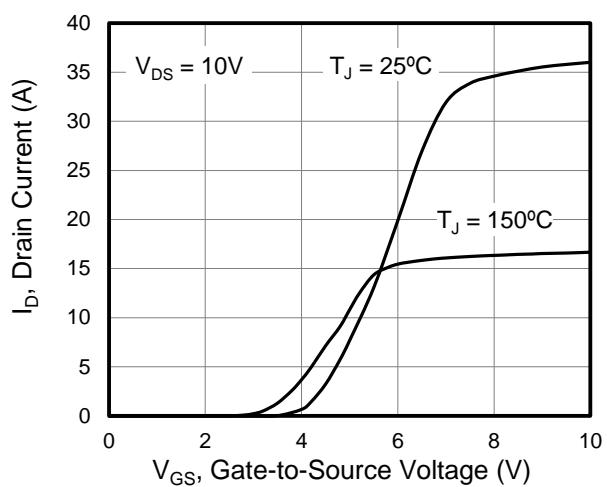


Figure 3. On-Resistance vs. Drain Current

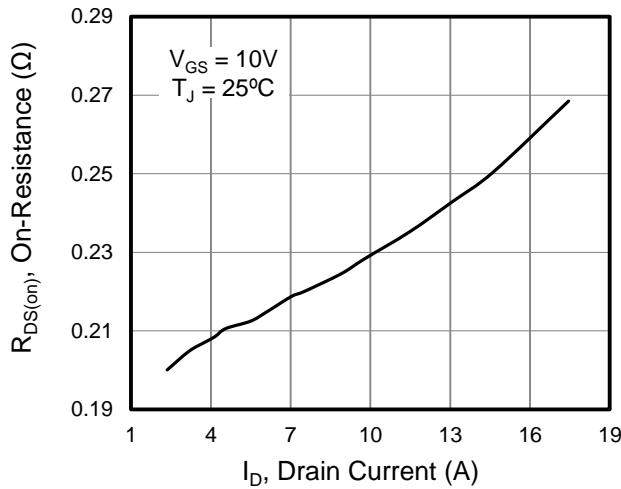


Figure 4. Capacitance

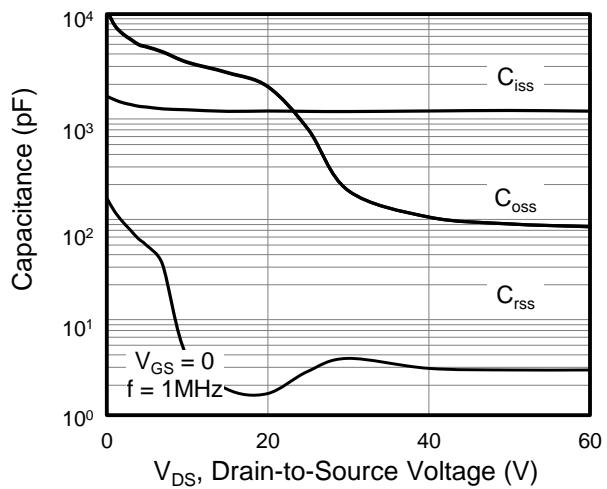


Figure 5. Gate Charge

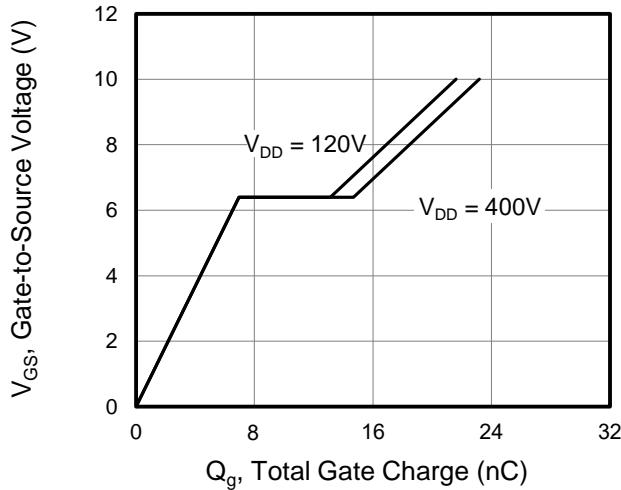


Figure 6. Body Diode Forward Voltage

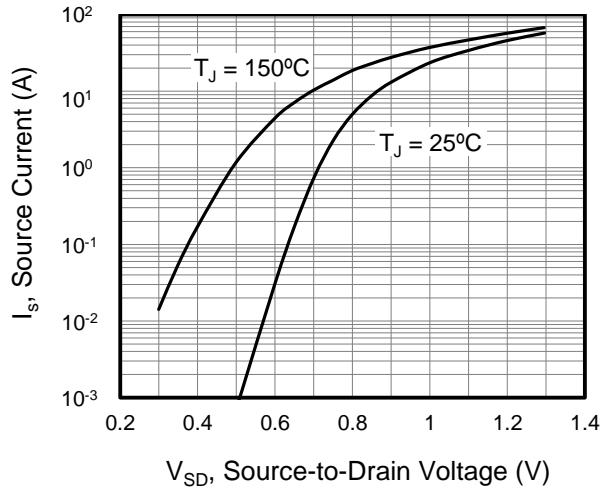


Figure 7. On-Resistance vs. Junction Temperature

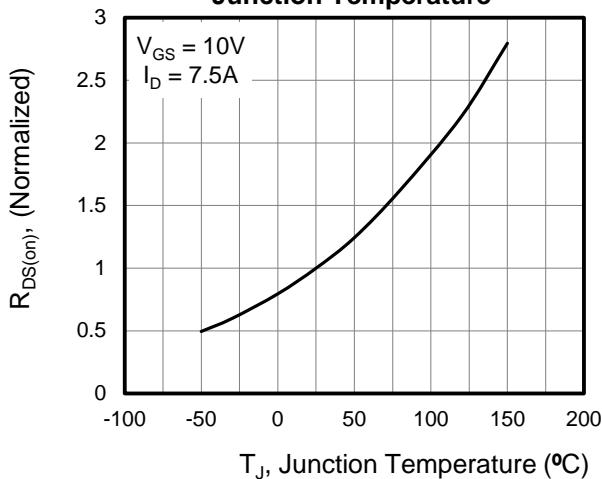


Figure 8. Threshold Voltage vs. Junction Temperature

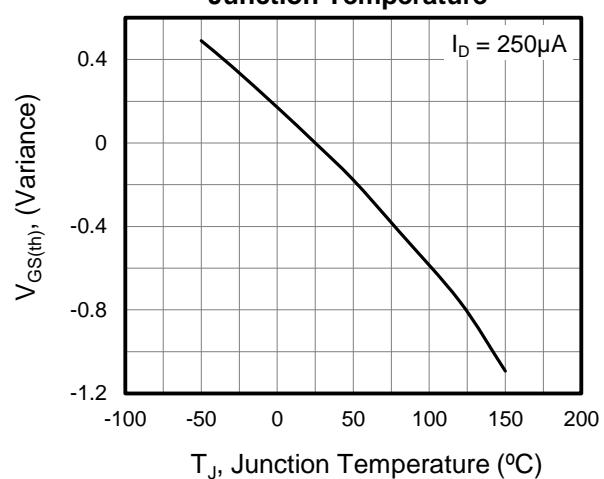


Figure 9. Transient Thermal Impedance TO-252

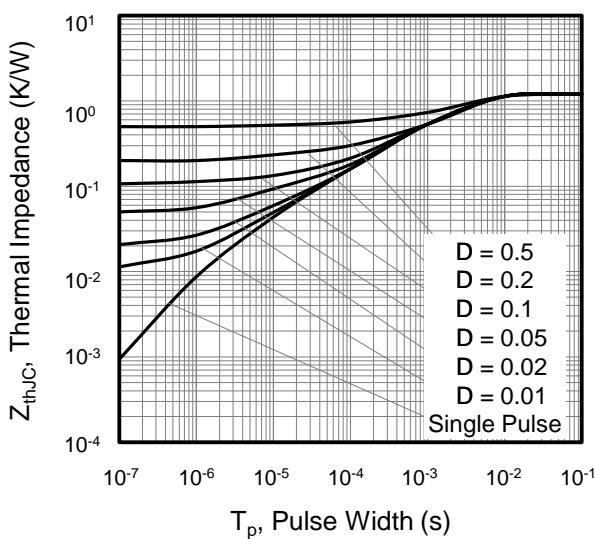


Figure 10. Transient Thermal Impedance TO-220F

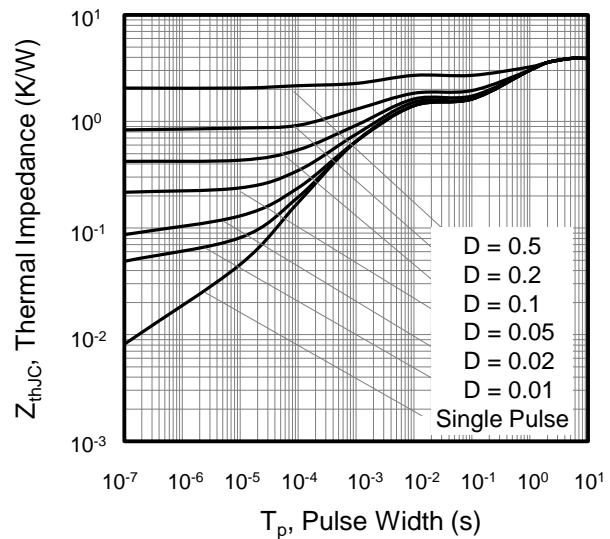


Figure 11. Safe operation area for TO-252

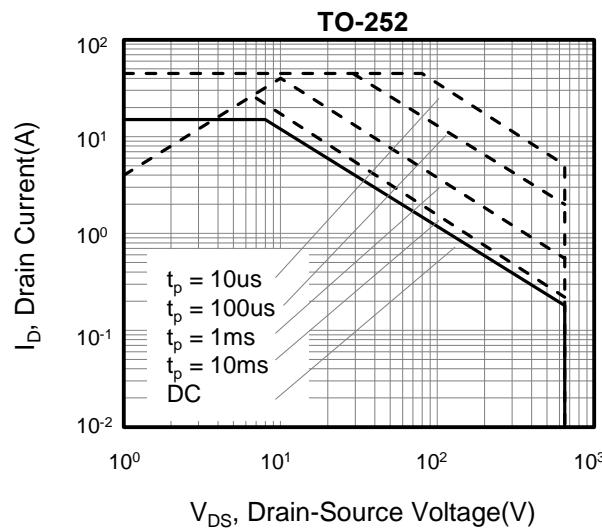
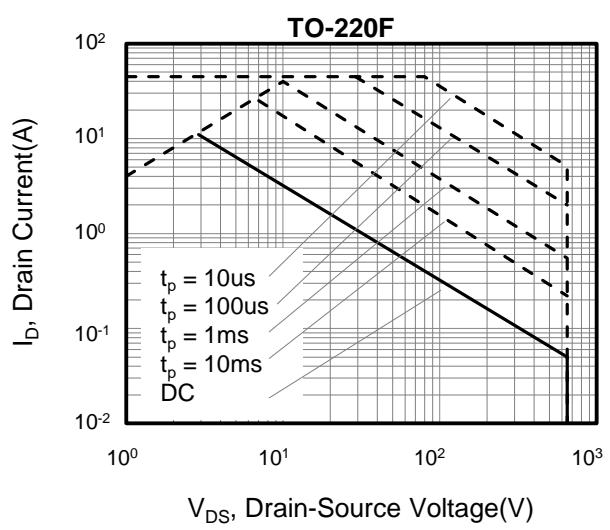
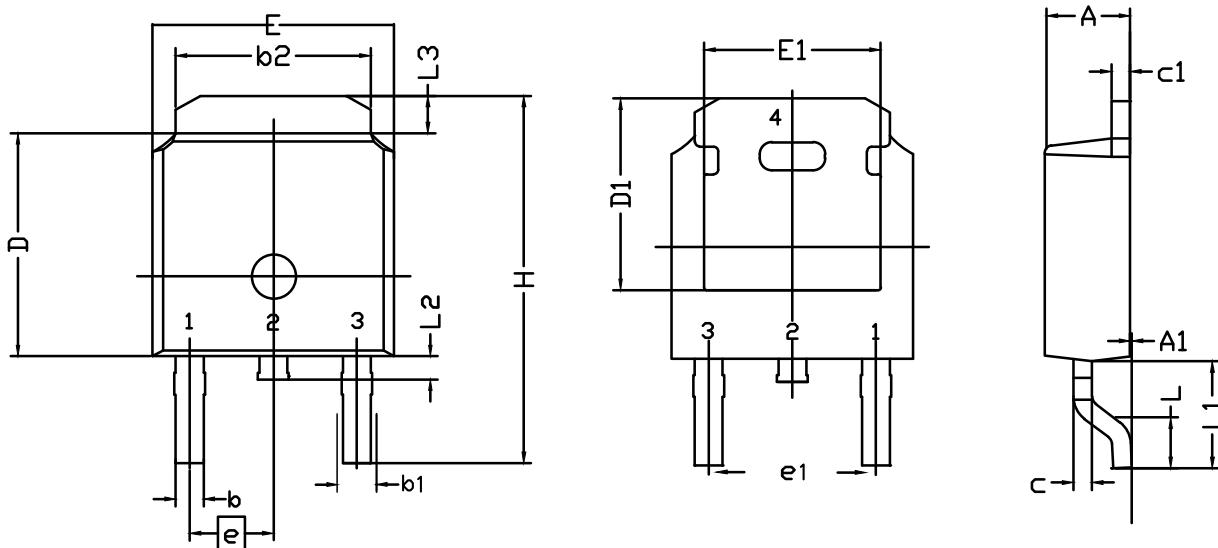
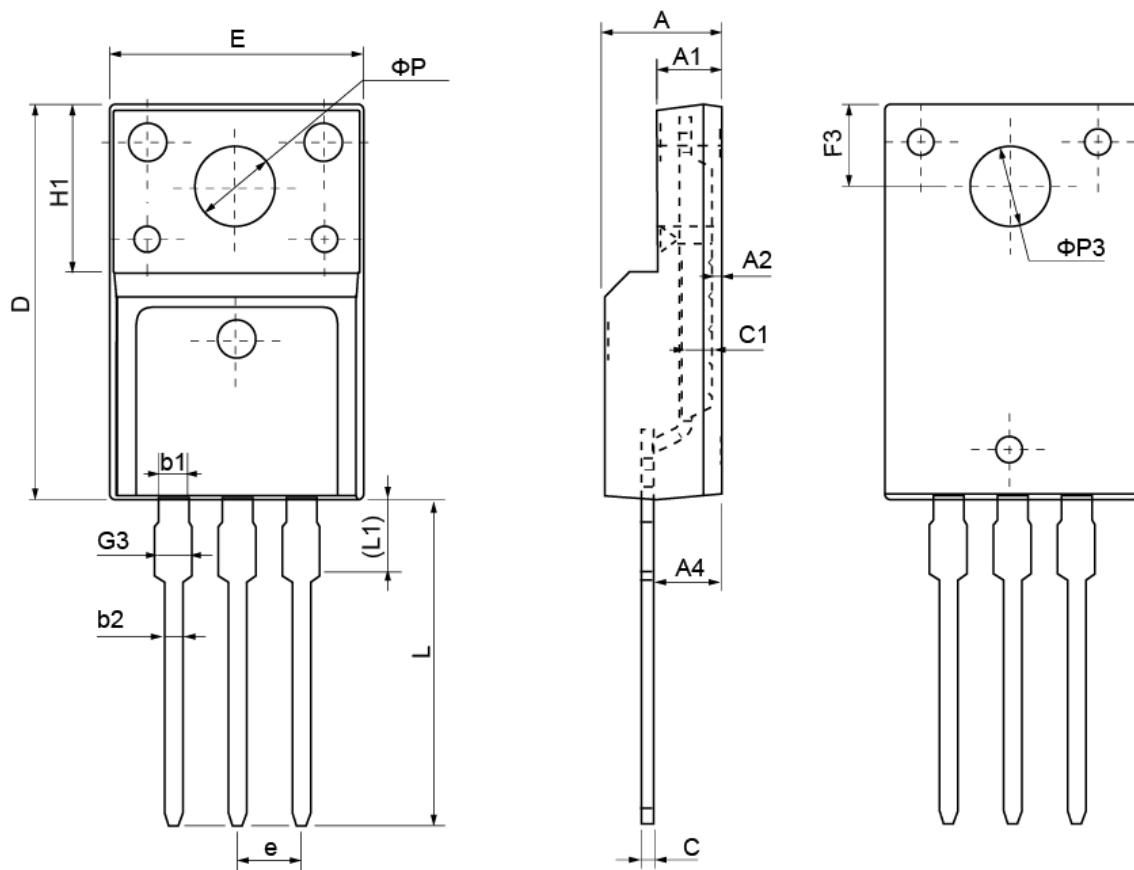


Figure 12. Safe operation area for TO-220F



TO-252 Package Outline Dimensions


Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	2.20	2.30	2.38	E	6.40	6.60	6.731
A₁	0.00	0.10	0.20	E₁	4.40	--	--
b	0.64	0.76	0.89	e	2.286 BSC		
b₁	0.77	0.85	1.14	e₁	4.572 BSC		
b₂	5.00	5.33	5.46	H	9.40	10.00	10.40
c	0.458	0.508	0.610	L	1.40	1.52	1.77
C₁	0.458	0.508	0.620	L₁	--	2.743	--
D	5.98	6.10	6.223	L₂	0.60	0.80	1.01
D₁	5.20	5.25	5.38	L₃	0.90	1.06	1.25

TO-220F Package Outline Dimensions


Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	4.40	4.70	5.00	H1	6.70 REF		
A1	2.30	2.55	2.80	L	12.30	12.98	13.30
A2	0.30	0.50	0.70	L1	2.95	3.10	3.50
A4	2.45	2.80	3.05	φ P	3.03	3.20	3.50
c	0.30	0.50	0.70	φ P3	3.15	3.45	3.65
c1	1.20	1.30	1.40	b1	1.10	1.30	1.45
D	15.40	15.90	16.40	b2	0.60	0.80	1.00
E	9.86	10.16	10.46	F3	3.05	3.30	3.55
e	2.54 BSC			G3	1.15	1.35	1.55